This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1-4 (canceled).

5 (new): A semiconductor device, which is formed by combining and disposing pre-registered functional blocks, and determining a wiring pattern in accordance with a given logic circuit specification, wherein:

each of the functional blocks has a logic circuit and a diode; and

the diode is composed of a first conduction type diffusion layer and a second conduction type well connected to a power source, the diode being connected to an input terminal, which is to be potential-clamped, among input terminals of the functional blocks.

6 (new): The semiconductor device as claimed in Claim 5, wherein the logic circuit is a memory.

7 (new): A method of designing a semiconductor device, which is formed by combining and disposing pre-registered functional blocks, and determining a wiring pattern in accordance with a given logic circuit specification, comprising the steps of:

registering the functional blocks in advance,

wherein each of the functional blocks has a logic circuit and a diode, and

wherein the diode is composed of a first conduction type diffusion layer and a second conduction type well connected to a power source, the diode being connected to an input terminal,

which is to be potential-clamped, among input terminals of the functional blocks.

8 (new): A computer-readable recording medium, on which the method of designing a semiconductor device, as claimed in Claim 7, is stored as a program to be executed by a computer.

9 (new): A design support apparatus for a semiconductor device, which is formed by combining and disposing pre-registered functional blocks, and determining a wiring pattern in accordance with a given logic circuit specification, comprising: registration means for registering the functional blocks in advance,
   wherein each of the functional blocks has a logic circuit and a diode, and
   wherein the diode is composed of a first conduction type diffusion layer and a second conduction type well connected to a power source, the diode being connected to an input terminal, which is to be potential-clamped, among input terminals of the functional blocks.